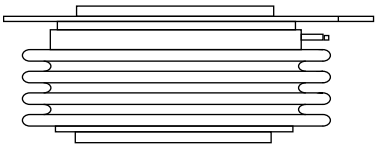
Phase Control Thyristors (Hockey PUK Version), 1473 A



A-24 (K-PUK)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Compliant to RoHS Directive 2002/95/EC

Pb-free

RoHS COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY	
$I_{T(AV)}$	1473 A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		1473	A
	T_{hs}	55	°C
$I_{T(RMS)}$		2913	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	20.0	A
	60 Hz	21.2	
I^2t	50 Hz	2000	kA^2s
	60 Hz	1865	
$I^2\sqrt{t}$		20 000	$kA^2\sqrt{s}$
V_{DRM}/V_{RRM}	Range	1200 to 2600	V
t_q	Typical	300	µs
T_J	Range	- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM}, MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT T_J = 125 °C mA
ST1000C..K	12	1200	1300	100
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	
	22	2200	2300	
	24	2400	2500	
	26	2600	2700	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave Double side (single side) cooled			1473 (630)	A
					55 (85)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled			6540	A
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	20.0	kA
		t = 8.3 ms			21.2	
		t = 10 ms	100 % V_{RRM} reapplied		17.0	
		t = 8.3 ms			18.1	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		2000	kA^2s
		t = 8.3 ms			1865	
		t = 10 ms	100 % V_{RRM} reapplied		1445	
		t = 8.3 ms			1360	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied			20 000	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.950	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.024	
Low level value of on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.283	mΩ
High level value of on-state slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.265	
Maximum on-state voltage drop	V_{TM}	I_{pk} = 3000 A, T_J = 125 °C, t_p = 10 ms sine pulse			1.80	V
Maximum holding current	I_H	T_J = 25 °C, anode supply 12 V resistive load			600	mA
Typical latching current	I_L				1000	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ µs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/µs
Typical delay time	t_d	Gate current 1 A, dI_g/dt = 1 A/µs V_d = 0.67 % V_{DRM}, T_J = 25 °C	1.9	µs
Typical turn-off time	t_q	I_{TM} = 550 A, $T_J = T_J$ maximum, dI/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 Ω, t_p = 500 µs	300	

BLOCKING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES TYP.	VALUES MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		16		W
Maximum peak average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, f = 50 Hz, d% = 50		3		W
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	+ V_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20		V
Maximum peak negative gate voltage	- V_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		5.0		V
DC gate current required to trigger	I_{GT}	T_J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	200	-	mA
		T_J = 25 °C		100	200	mA
		T_J = 125 °C		50	-	mA
DC gate voltage required to trigger	V_{GT}	T_J = - 40 °C		1.4	-	V
		T_J = 25 °C		1.1	3.0	V
		T_J = 125 °C		0.9	-	V
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	°C
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.042	K/W
		DC operation double side cooled	0.021	K/W
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled	0.006	K/W
		DC operation double side cooled	0.003	K/W
Mounting force, ± 10 %			24 500 (2500)	N (kg)
Approximate weight			425	g
Case style		See dimensions - link at the end of datasheet	A-24 (K-PUK)	

ΔR_{thJC} CONDUCTION

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.003	0.003	0.002	0.002	$T_J = T_J$ maximum	K/W
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

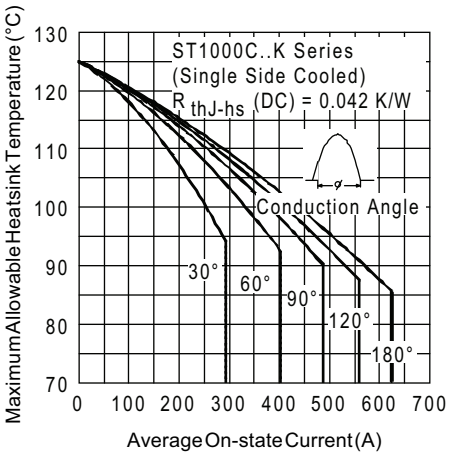


Fig. 1 - Current Ratings Characteristics

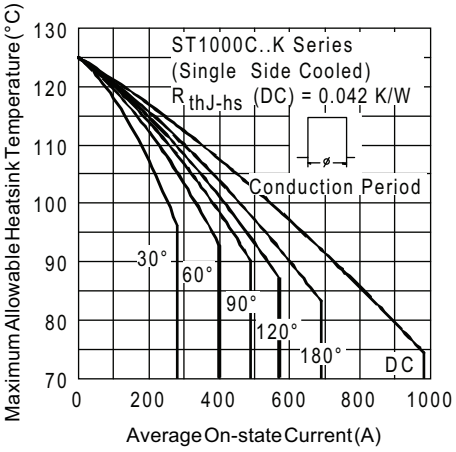


Fig. 2 - Current Ratings Characteristics

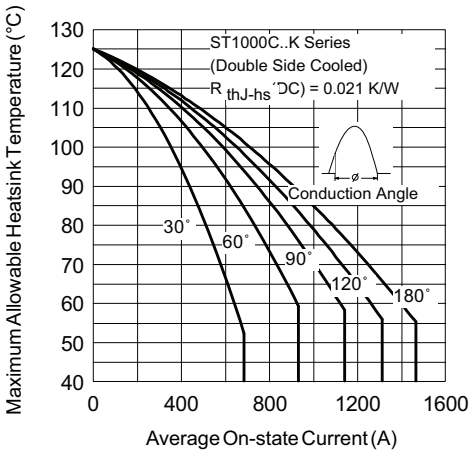


Fig. 3 - Current Ratings Characteristics

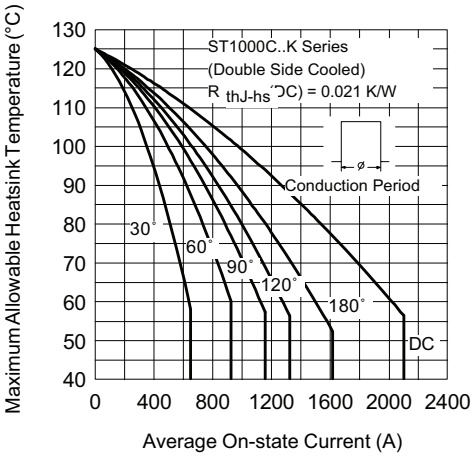


Fig. 4 - Current Ratings Characteristics

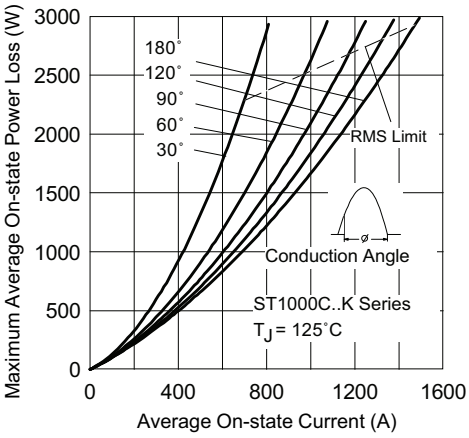


Fig. 5 - On-State Power Loss Characteristics

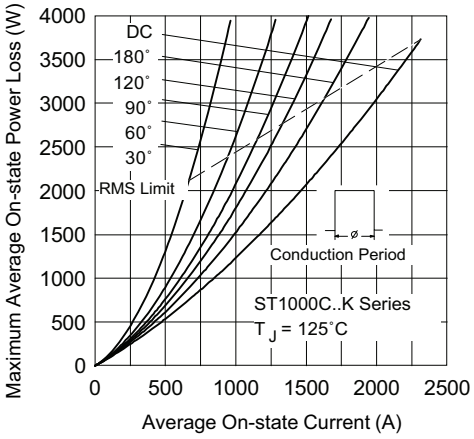


Fig. 6 - On-State Power Loss Characteristics

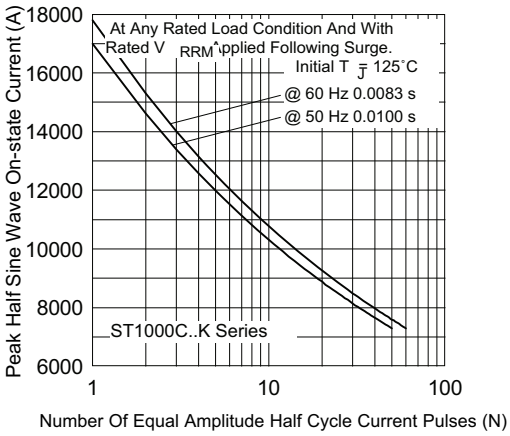


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

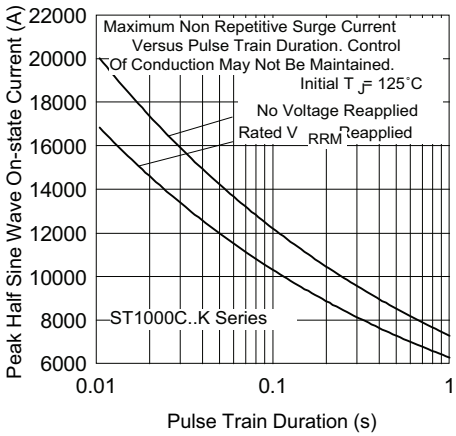


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

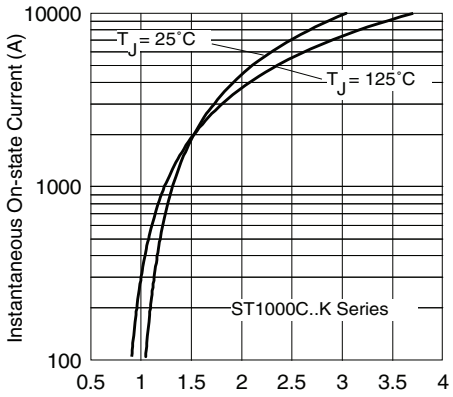


Fig. 9 - On-State Voltage Drop Characteristics

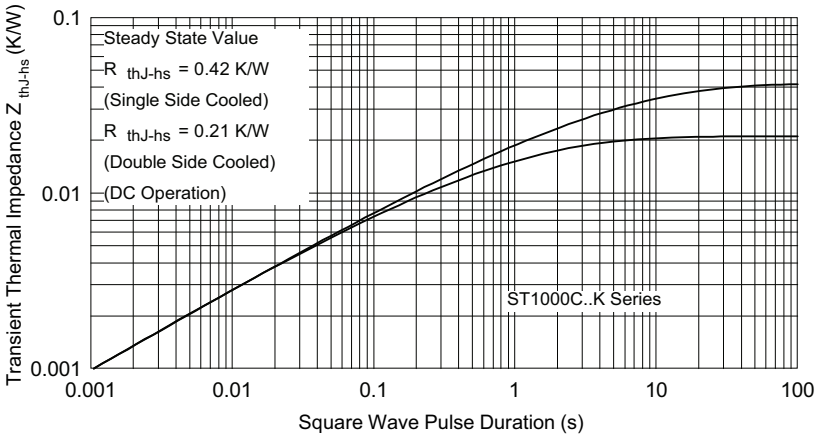


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

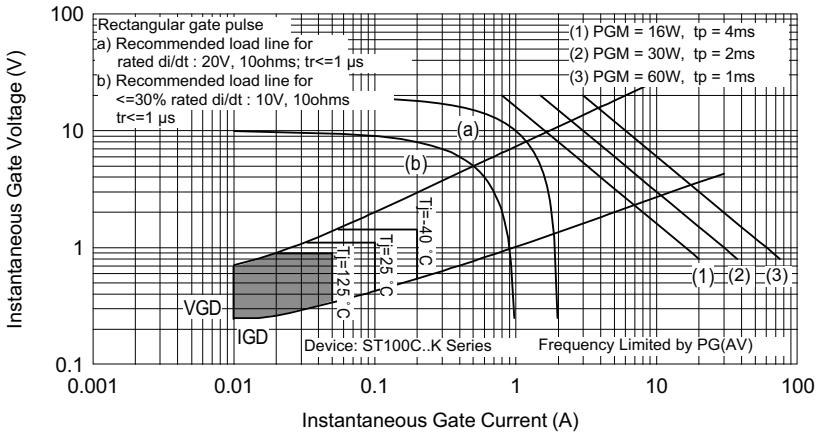


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

ST	100	0	C	26	K	1	-
1	2	3	4	5	6	7	8

1 - Thyristor

2 - Essential part number

3 - 0 = Converter grade

4 - C = Ceramic PUK

5 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

6 - K = PUK case A-24 (K-PUK)

7 - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
3 = Fast-on terminals (gate and auxiliary cathode soldered leads)

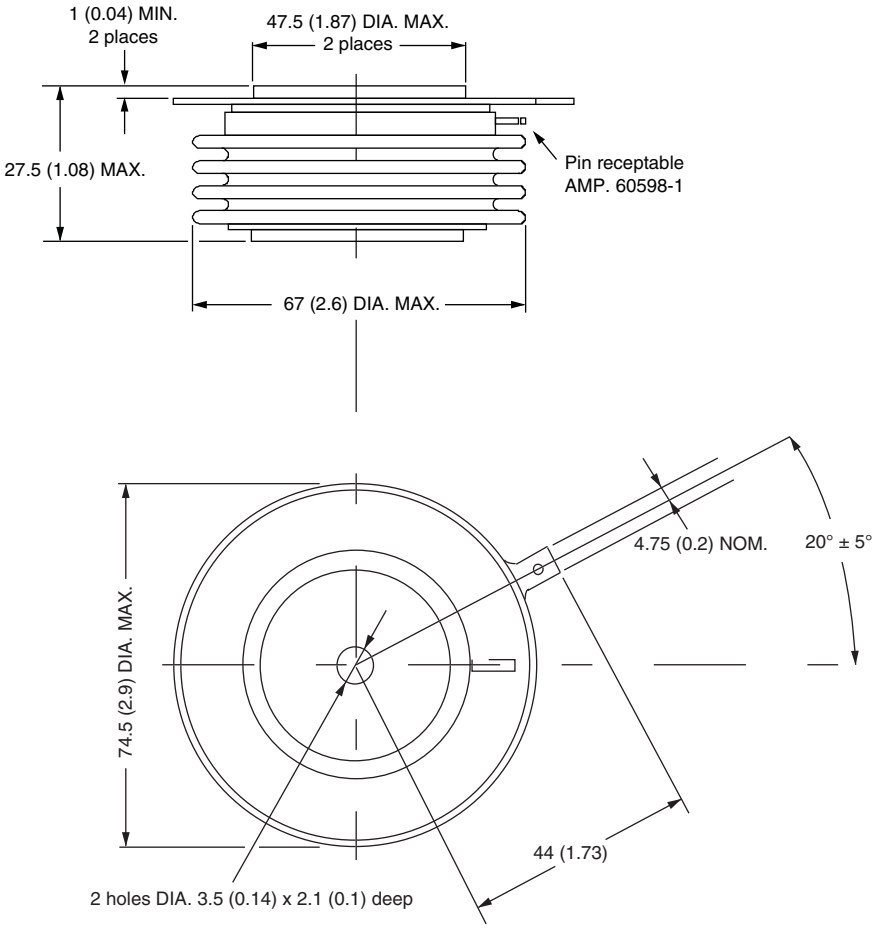
8 - Critical dV/dt: • None = 500 V/µs (standard selection)
• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95081

A-24 (K-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum
Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)

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